风光欣技术资料

A1317S

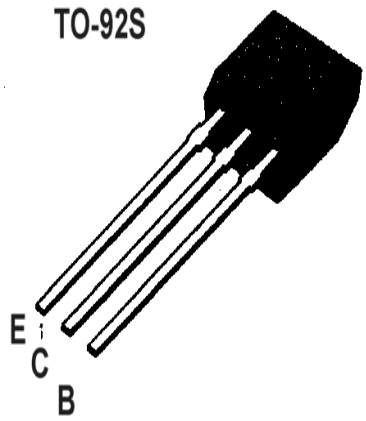
PNP Transistors

—PNP Silicon—

■■ **APPLICATION：** Frequency Applications.

■■ **MAXIMUM RATINGS**（Ta=25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	Ic	-0.2	A
	Icp	-0.4	A
Collector Power Dissipation	Pc	0.3	W
Junction Temperature	Tj	150	℃
Storage Temperature Range	Tstg	-55~150	℃



■■ **ELECTRICAL CHARACTERISTICS**（Ta=25℃，RG=10Ω）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION	
Collector-Base Breakdown Voltage	BVcbo	-60			V	Ic=-50uA	Ie=0
Collector-Emitter Breakdown Voltage	BVceo	-50			V	Ic=-1mA	Ib=0
Emitter-Base Breakdown Voltage	BVebo	-6			V	Ie=-50uA	Ic=0
Collector Cut-off Current	Icbo			-0.1	uA	Vcb=-40V	Ie=0
Collector-Emitter Saturation Voltage	Iebo			-0.1	uA	Veb=-5V	Ic=0
Base-Emitter Saturation Voltage	Vbe(sat)			-1	V	Ic=-0.1A	Ib=-10mA
Collector-Emitter Saturation Voltage	Vce(sat)			-0.3	V	Ic=-0.1A	Ib=-10mA
DC Current Gain	h_{FE}	100		560	β	Vce=-6V	Ic=-1mA
Gain bandwidth product	f_T		200		MHz	Vce=-6V	Ic=-10mA
Common Base Output Capacitance	Cob		4		pF	Vcb=-6V	I_E=0f=1MHz

■■hFE **Classification And Marking**

Print Mark	A1317S			
Classification	R	S	T	U
h_{FE}	100~200	140~280	200~400	280~560